



BOX AFTER FINAL  
EXPEDITED PROCEDURE  
740756-1638

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Re PATENT application of:

Hisashi OHTANI et al.

Application No.: 08/807,737

Filed: February 27, 1997

For: METHOD FOR MANUFACTURING  
SEMICONDUCTOR DEVICE

Art Unit: 2813

Examiner: Evan PERT

#44/501  
9/25/01  
V. Varnall

AMENDMENT AFTER FINAL UNDER 37 C.F.R. 1.116

Commissioner of Patents  
Washington, D.C. 20231

September 19, 2001

Dear Sir:

In response to the Examiner's Final Office Action mailed May 9, 2001, please consider the following remarks in connection with the above-identified application.

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IN THE CLAIMS:

Please amend claim 84 as follows:

84. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a silicon nitride film containing at least one of hydrogen and oxygen over a substrate;

depositing a semiconductor film comprising amorphous silicon on said silicon nitride film;

disposing a metal contact with at least a selected portion of said semiconductor film;